

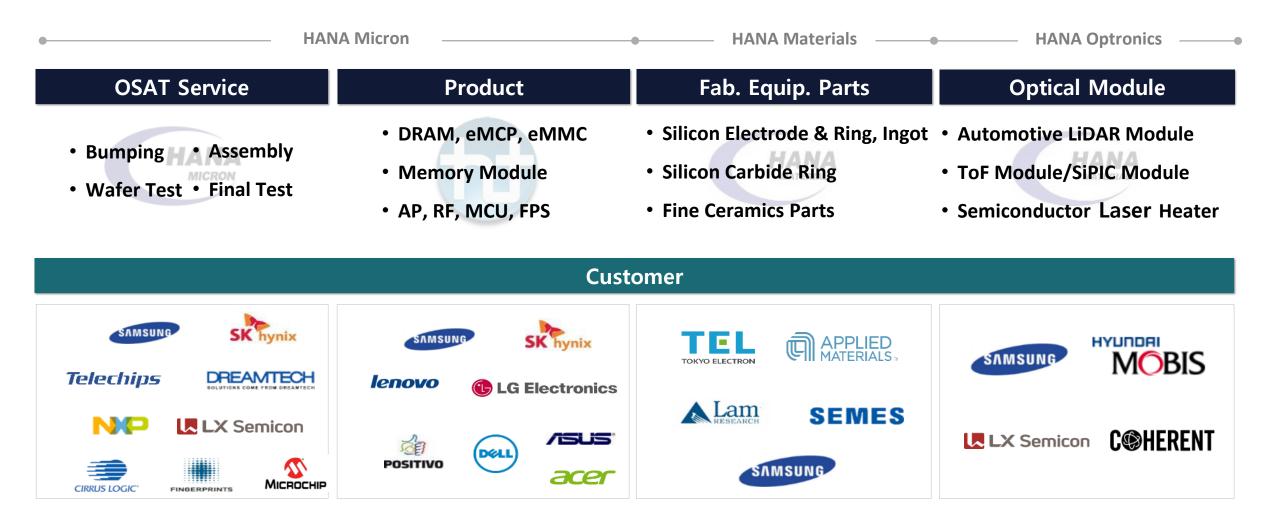
Designing Chiplet-Based 2.5D High-Interconnect Density Semiconductor Packages:

Challenges and Considerations

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HANA Micron Corporate Overview

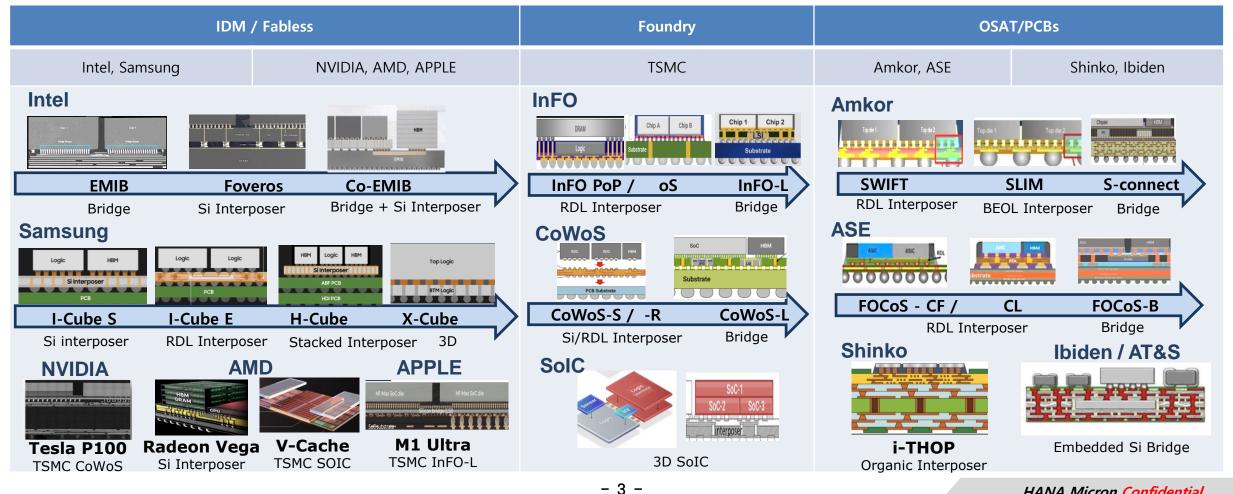
"HANA Micron is a leading Semiconductor Package Turnkey Solution Provider in Korea"



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Chiplet Based Advanced Packaging Technology Overview

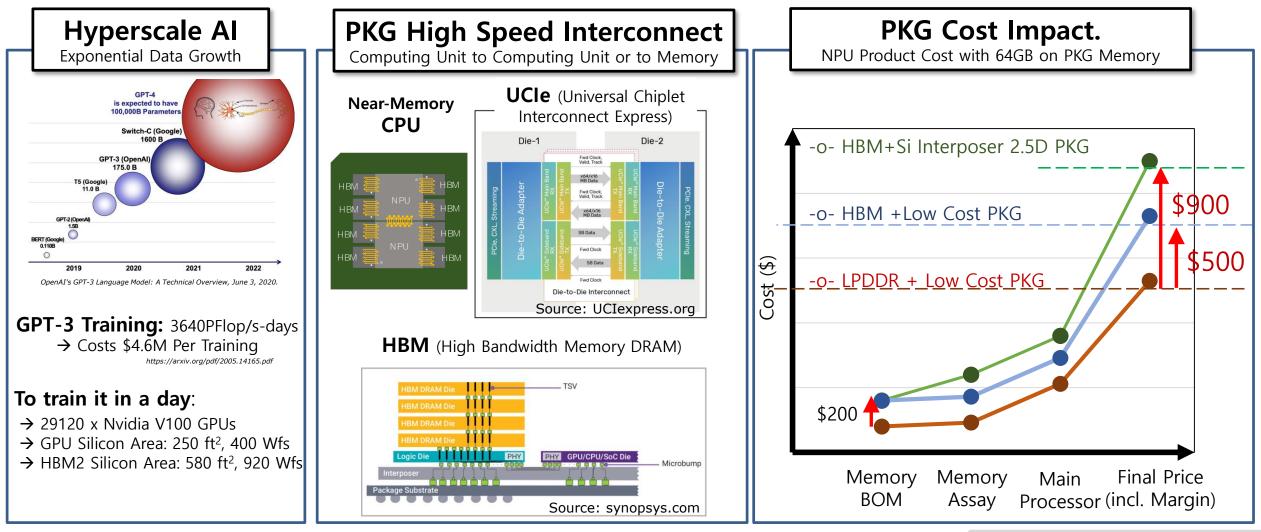
- Foundries and IDMs : Developing in-house and Establishing a Tech. Platform including 3D and 2.5D \rightarrow preventing true heterogeneous integration of chiplets from different foundries.
- **OSATs**: Focusing on Backend 2.5D Integration. Silicon Interposer, RDL Interposer and Silicon Bridge



Demand for Interconnect Standard & Low Cost 2.5D Tech. Solution

• Al Computing Power : outpaces Moore's law.

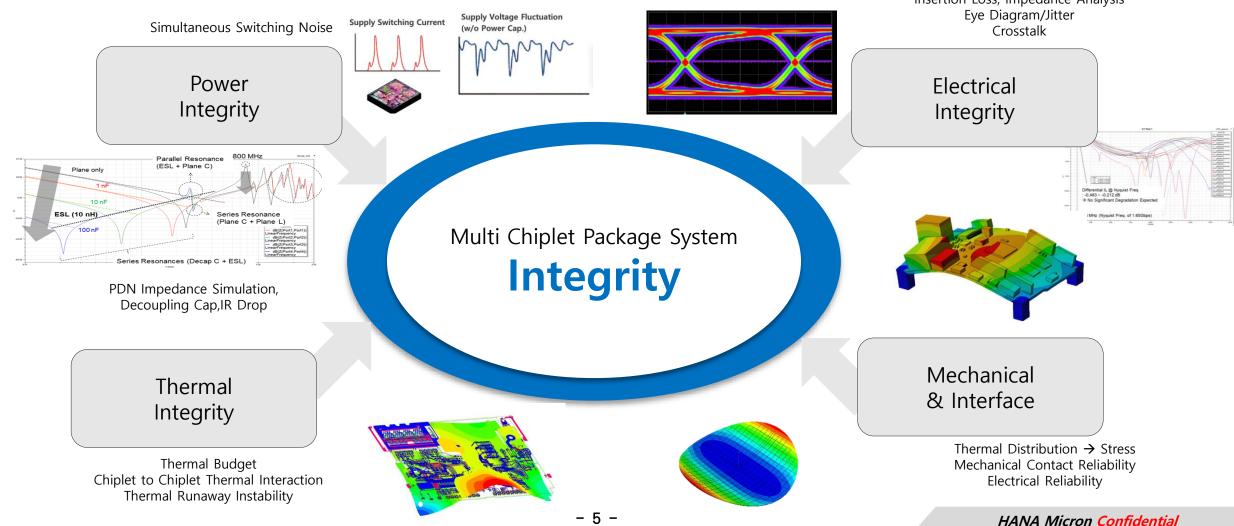
 \rightarrow In-PKG Interconnect standard for lower design cost and OSAT need to develop low cost PKG technology.



Package Design Verification

□ Interaction Verification

User-friendly design flows require the creation of signal, power, thermal and mechanical models for the IC, package and PCB which are then combined for system-level simulation.

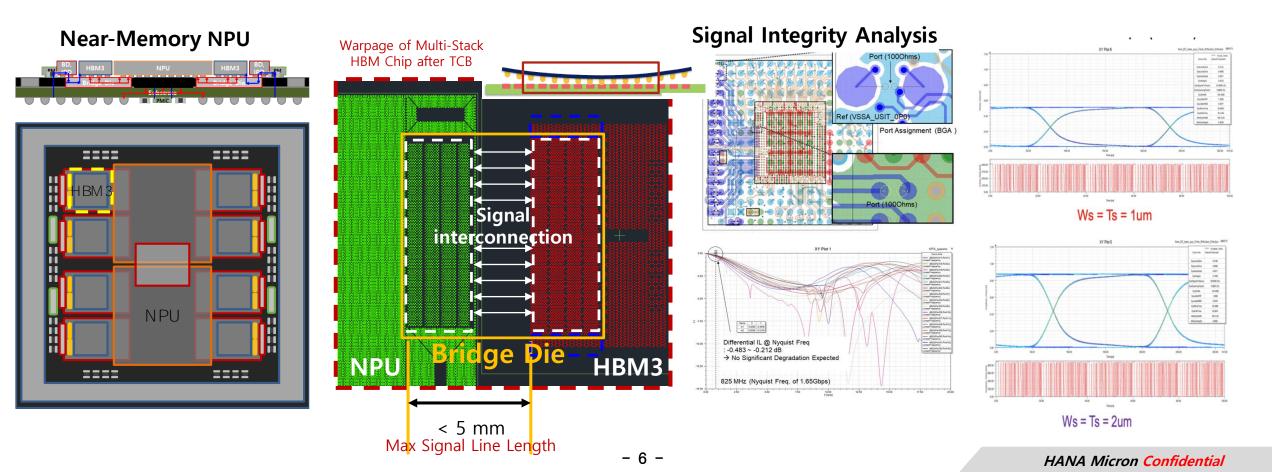


Near Memory NPU – HBM3 Signal Line Design

□ HBM3 chip dimension: > 3000 I/Os per 8mm Signal Width & max 5mm Signal Line

□ **SI Anlaysis:** due to large insertion loss (Long Signal Line), L/S >2um Signal Line needed.

 \rightarrow Limiting Linear Escape Density to 250 I/O per mm-Layer, SERDES needed for future Gen.



3D Stacked Memory drastically boost Bandwidth

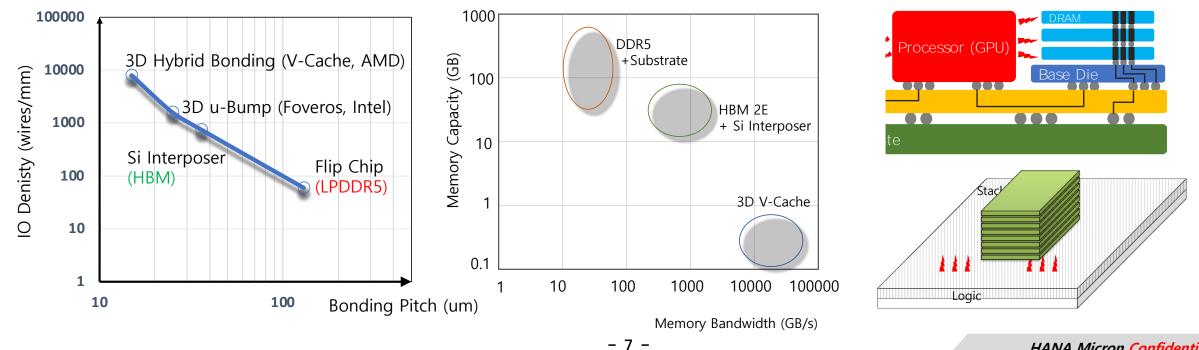
3D Stacked Memory on Processor: Highest Memory Bandwidth Possible.

 \rightarrow AMD's V Cache SRAM: <32MB. Too small for large parameter deep learning.

HBM on Processor or Processor in HBM: DRAM's operating temperature is limited < 85C°

 \rightarrow Processing unit's performance is limited by thermal budget.

High Operating Temperature + High Speed + High Density Memory + High Endurance Needed

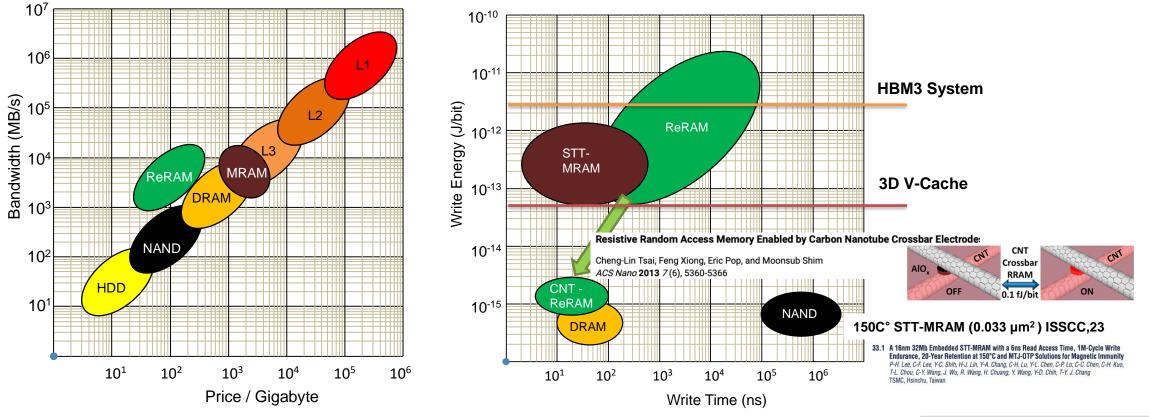


3D Stackable Memory Candidates

□ MRAM and ReRAM have potentials: Similar cost and read bandwidth to DRAM.

- \rightarrow Nano-technology (ex. CNT) might help reducing the Write Energy.
- \rightarrow By sacrificing retention, operating temperature might be increased.

□ Further New Memory Device Research needed for more efficient AI Processor.

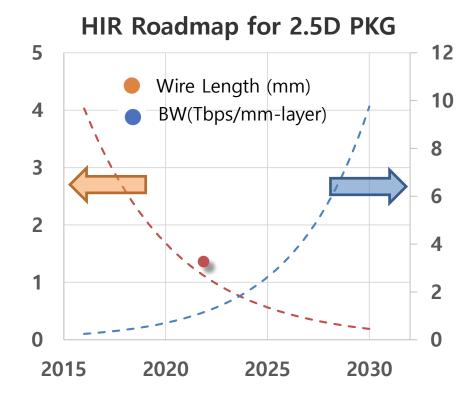


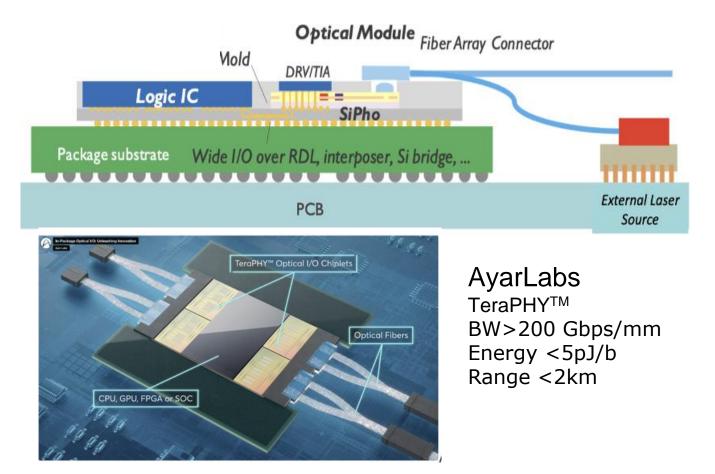
Optical Interconnects between Chip Packages

CPO (Co-Packaged Optics): Silicon Photonics in Chiplet PKG.

→ Waveguide, Modulator, PD, WDM Filter, DeMux, Coupler etc.

BW Target: >1Tbps/mm @ distance up to a few km (w/2.5D requires <5mm short distance)





Conclusion

□ OSATs are developing low cost 2.5D Advanced Packaging Technology.

- Power, Electrical, Thermal and Stress integrities must be thoroughly examined.
- □ 3D Stacking of Memory to drastically improve the Memory Bandwidth
- □ Novel Memory operating at higher temperature is needed
- □ Optical Interconnect started to be co-integrated in same package.
- □ Collaboration with USA research group played a vital role.
- \rightarrow Past a few years, worked with USA Universities on optoelectronics projects funded by Korean Government.
- → Collaboration ended due to classification of the project as a National Security Tech.
- \rightarrow Advanced Packaging Technology is currently classified as a National Core Tech.

□ In Semiconductor Advanced Packaging Field, NSF and Korea Government Joint Research Program would facilitate further collaboration between two countries.